WG6 Work Package Project

Title: SiC Material Studies with pad and strip sensors

Project description

Wide band-gap (WBG) semiconductors are increasingly dominating the power device market, with significantly enhanced material quality. Silicon Carbide is the material used for HV power devices and would also be an attractive particle detector material due to the low leakage current of the ulta, even after irradiation. However, the material is more challenging due to anisotropy effects and a high defect concentration already in the unirradiated case. Moreover, many material parameters are not well known or described in the literature as a mix of the different polytypes. Thus, a systematic material characterization study is necessary to bring SiC to a comparable level of understanding as it exists for silicon. For this purpose, this project aims to produce a large number of simple, planar diodes that can be used for an extensive irradiation and characterization study, covering IV, CV, and CEE measurements by SPA and TPA-TCT techniques, as well as beam tests. For this purpose, FBK starts a new production line on SiC devices, which this project will qualify in parallel. Moreover, trap levels and concentrations will be studied using TSC and DLTS techniques, providing input to an irradiation model. After passing this step, also the possibility of implementing a gain layer in the devices will be evaluated, with thorough studies of impact ionization mechanisms and the behaviour of it under irradiation. This project aligns with the ECFA DRDT 3.2 (Sensors for 4D-tracking) and DRDT 3.3 (Sensors for extreme fluences) and the DRD3 research goals 6.2.

Number	Title	Description	Start date	End date	Institutions
Di.1	Fabrication of Schottky Devices	First production run at FBK			
Di.2	Fabrication of PIN Devices	Fabrication of junction devices at FBK			
Di.3	Electronics Readout	Development of readout single			
Di.4	Characterization	<i>Characterization of IV, CV, Charge collection, time resolution test, beam tests</i>			
Di.5	Irradiation	Irradiate SiC-LGAD devices up to 1×10 ¹⁸ n _{eq} /cm2			
Di.6	Study of Irradiation Defects and irradiation model				

Milestones, deliverables and timeline

Participating Institutions

Country	Collaborating Institution	Town	Institution Code	Contact	
Austria	OEAW-HEPHY		HEPHY	Thomas Bergauer	
Switzerland	vitzerland CERN CERN				
Romania	NIMP Bucharest		NIMP	Ioana Pintilie	
Italy	INFN Torino		Torino	Valentina Sola	
Italy	INFN Perugia		Perugia	Francesco Moscatelli	
Italy	FBK		FBK	Maurizio Boscardin	

Collaborative work:

The characterisation of irradiated and non-irradiated devices will be done in collaboration of WG2, WG3 and WG5, modelling of radiation damage will be done in collaboration with WG4. Dissemination and outreach will be done in WG8. Possible cross-DRD studies with DRD7.

Potential synergies with similar projects: RD50: SiC-LGAD, SiC-LGAD-TPIX, TCAD Radiation Damage Model for 4H-SiC, Defect characterization on 4H-SiC sensors.

Funding Agencies

Country	Funding Agency	Funding Agency Code	Representative	Institution(s) represented

Contributions of Participating Institutions and Funding Agencies to the Work Package

	Deliverable											
	Di1		Di2		Di3			Total				
Institution / Funding Agency	Material / kCHF	Physicists: FTE months	Engineers and technicians: FTE months	Material / kCHF	Physicists: FTE months	Engineers and technicians: FTE months	Material / kCHF	Physicists: FTE months	Engineers and technicians: FTE months	Material / kCHF	Physicists: FTE months	Engineers and technicians: FTE months
			Major	(e.g. na	ational)	Fundin	g Agen	cies				
	60	10	20	60	10	20						
Total Major Funding Agencies												
			Cor	ntributi	ons froi	n other	sources	5				<u> </u>
DEF via Institution 5												
GHI via Institution 6												
Total other sources												
Total (Major Funding Agencies plus other sources)												

	Total		
Di4	Di5	Di6	Total

Institution / Funding Agency	Material / kCHF	Physicists: FTE months	Engineers and technicians: FTE months	Material / kCHF	Physicists: FTE months	Engineers and technicians: FTE months	Material / kCHF	Physicists: FTE months	Engineers and technicians: FTE months	Material / kCHF	Physicists: FTE months	Engineers and technicians: FTE months
			Major	' (e.g. na	ational)	Fundin	g Ageno	cies				
		10	20					10	20			
Total Major Funding Agencies												
			Сог	ntributi	ons froi	n other	sources	6			I	<u> </u>
DEF via Institution 5												
GHI via Institution 6												
Total other sources												
Total (Major Funding Agencies plus other sources)												

Project structure

Function	Name
Work Package Leader	TBD
Work Package Deputy Leader	TBD